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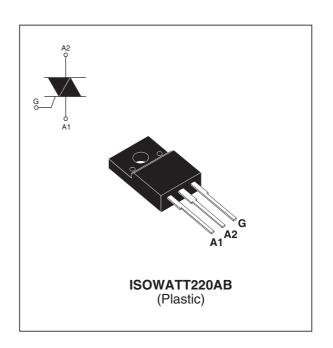
## 16A SNUBBERLESS™ TRIAC

#### **MAIN FEATURES**

Symbol	Value	Unit	
I <sub>T(RMS)</sub>	16	А	
V <sub>DRM</sub> /V <sub>RRM</sub>	600 and 800	V	
I <sub>GT</sub>	20 to 30	mA	

#### **DESCRIPTION**

Based on ST' Snubberless technology providing high commutation performances, the T1620-600W/800W & T1630-600W/800W are specially recommended for use on inductive loads, thanks to their high commutation performances, such as vacuum cleaners, heating regulation. They comply with UL standards (ref. E81734).



## **ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit		
I <sub>T(RMS)</sub>	RMS on-state current (Full sine wave) Tc= 80°C			16	Α
I <sub>TSM</sub>	Non repetitive surge peak on-state	F = 50Hz	t = 20ms	200	Α
	current (Full cycle, $T_j$ initial = 25°C)	F = 60Hz	t = 16.7ms	218	
I <sup>2</sup> t	I <sup>2</sup> t Value for fusing	tp = 10	) ms	220	A <sup>2</sup> s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $tr \le 100 \text{ns}$ $I_G = 2 \times I_{GT}$		Tj = 125°C	50	A/μs
V <sub>DSM</sub> /V <sub>RSM</sub>	Non repetitive surge peak off-state tp = 10ms Tj = 2 voltage		Tj = 25°C	V <sub>DRM</sub> /V <sub>RRM</sub> + 100	V
I <sub>GM</sub>	Peak gate current tp = 20µs Tj = 125°C			4	Α
P <sub>G(AV)</sub>	Average gate power dissipation Tj = 125°C			1	W
T <sub>stg</sub> T <sub>j</sub>	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C

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## **ELECTRICAL CHARACTERISTICS** (Tj = 25°C, unless otherwise specified)

Symbol	Test Conditions	Quadrant		T1620	T1630	Unit
I <sub>GT</sub> <sup>(1)</sup>	$V_D=12V R_L=30\Omega$	1-11-111	MAX.	20	30	mA
$V_{GT}$		1-11-111	MAX.	1.3	1	V
$V_{GD}$	$V_D=V_{DRM}$ R <sub>L</sub> =3.3k $\Omega$ Tj = 125°C I-II-III		MIN.	0.2		V
I <sub>H</sub> <sup>(2)</sup>	I <sub>T</sub> = 250mA		MAX.	35	50	mA
lμ	$I_G = 1.2I_{GT}$	I - III	MAX.	70	80	mA
		II	MAX.	80	100	mA
dV/dt (2)	V <sub>D</sub> =67% V <sub>DRM</sub> Gate open Tj = 125°C		MIN.	300	500	V/μs
(dl/dt)c (2)	Without snubber Tj = 125°C		MIN.	8.5	11	A/ms

#### STATIC CHARACTERISTICS

Symbol	Symbol Test Conditions			Value	Unit
V <sub>TM</sub> <sup>(2)</sup>	$I_{TM} = 22.5 \text{ A}$ tp = 380µs	Tj = 25°C	MAX.	1.4	V
V <sub>TO</sub> <sup>(2)</sup>	Threshold voltage	Tj = 125°C	MAX.	0.85	V
R <sub>d</sub> <sup>(2)</sup>	Dynamic resistance	Tj = 125°C	MAX.	20	mΩ
I <sub>DRM</sub> I <sub>RRM</sub>	$V_{DRM} = V_{RRM}$	Tj = 25°C Tj = 125°C	MAX	5 1	μA mA

Note 1: Minimum IGT is guaranted at 5% of IGT max. Note 2: For both polarities of A2 referenced to A1.

### THERMAL RESISTANCES

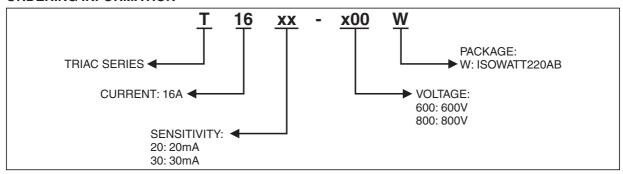
Symbol	Parameter	Value	Unit
Rth(j-a)	Junction to ambient	60	°C/W
Rth(j-c)	Junction to case (AC)	3.1	°C/W

## **PRODUCT SELECTOR**

Part Number	Voltage	Sensitivity	Туре	Package
T1620-600W	600V	20 mA	Snubberless	ISOWATT220AB
T1620-800W	800V	20 mA	Snubberless	ISOWATT220AB
T1630-600W	600V	30 mA	Snubberless	ISOWATT220AB
T1630-800W	800V	30 mA	Snubberless	ISOWATT220AB

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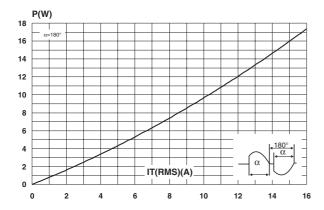
#### **ORDERING INFORMATION**



#### **OTHER INFORMATION**

Part Number	Marking	Weight	Base quantity	Packing mode
T1620-600W	T1620600W	2.3 g	50	Tube
T1620-800W	T1620800W	2.3 g	50	Tube
T1630-600W	T1630600W	2.3 g	50	Tube
T1630-800W	T1630800W	2.3 g	50	Tube

Fig. 1: Maximum power dissipation versus RMS on-state current.



**Fig. 3:** Relative variation of thermal impedance versus pulse duration.

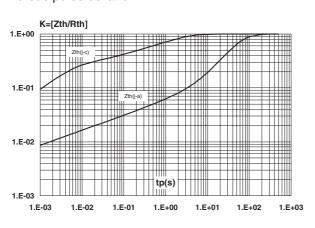


Fig. 2: RMS on-state current versus case temperature.

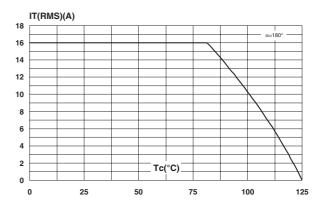
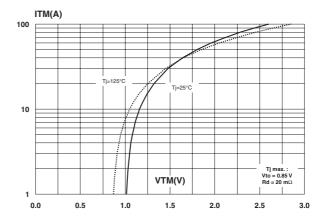
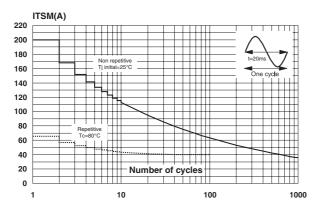


Fig. 4: On-state characteristics (maximum values).

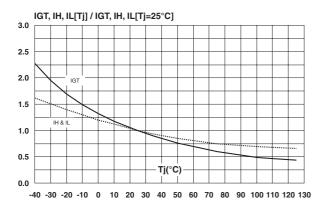


 $\overline{\mathbf{A}}$ 

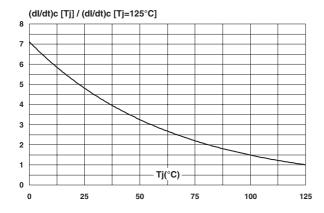
Fig. 5: Surge peak on-state current versus number of cycles.



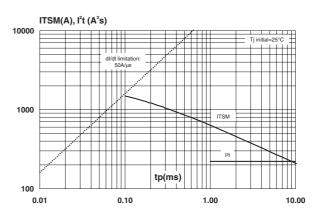
**Fig. 7:** Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).



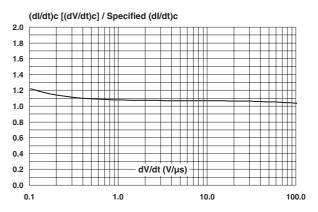
**Fig. 9:** Relative variation of critical rate of decrease of main current versus junction temperature.



**Fig. 6:** Non repetitive surge peak on-state current for a sinusoidal pulse with width tp<10ms, and corresponding value of  $I^2$ t.



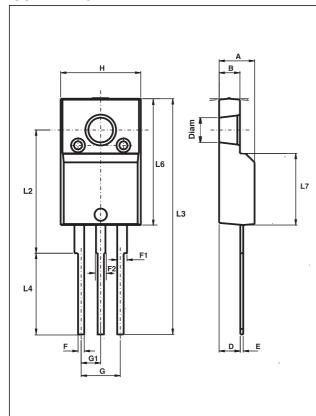
**Fig. 8:** Relative variation of critical rate of decrease of main current versus reapplied dV/dt (typical values).



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#### PACKAGE MECHANICAL DATA

ISOWATT220AB



	DIMENSIONS				
REF.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
В	2.50	2.70	0.098	0.106	
D	2.50	2.75	0.098	0.108	
E	0.40	0.70	0.016	0.028	
F	0.75	1.00	0.030	0.039	
F1	1.15	1.70	0.045	0.067	
F2	1.15	1.70	0.045	0.067	
G	4.95	5.20	0.195	0.205	
G1	2.40	2.70	0.094	0.106	
Н	10.00	10.40	0.394	0.409	
L2	16.00 typ.		0.630	O typ.	
L3	28.60	30.60	1.125	1.205	
L4	9.80	10.60	0.386	0.417	
L6	15.90	16.40	0.626	0.646	
L7	9.00	9.30	0.354	0.366	
Diam	3.00	3.20	0.118	0.126	

■ Cooling method : C

Recommended torque value : 0.55 m.N.

■ Maximum torque value : 0.70 m.N.

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